

SPTECH Product Specification

SPTECH Silicon PNP Darlington Power Transistor

TIP147

DESCRIPTION

- High DC Current Gain-
: $h_{FE} = 1000(\text{Min}) @ I_C = -5\text{A}$
- Collector-Emitter Sustaining Voltage-
: $V_{CE0(\text{SUS})} = -100\text{V}(\text{Min})$
- Complement to Type TIP142

APPLICATIONS

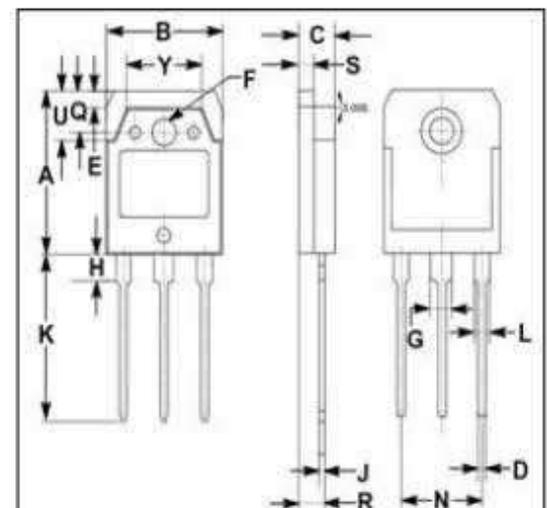
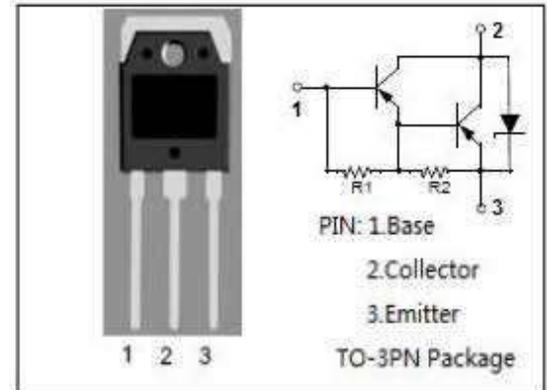
- Designed for general purpose amplifier and low frequency switching applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CB0}	Collector-Base Voltage	-100	V
V_{CE0}	Collector-Emitter Voltage	-100	V
V_{EB0}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-15	A
I_B	Base Current- Continuous	-0.5	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	125	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R_{thj-c}	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C}/\text{W}$
R_{thj-a}	Thermal Resistance, Junction to Ambient	35.7	$^\circ\text{C}/\text{W}$



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

